| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|----------|--------|---------------------------------|---|---------------------|---------|------------------|
| L1 | 103466 | vertical and transistor | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/30 19:06 |
| L2 | 39769 | 1 and gate and source and drain | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/30 19:06 |
| L3 | 267 | 2 and (carbon adj nanotube) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/30 19:06 |
| L4 | 106 | 3 and column and row | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/30 19:07 |
| L5 | 97 | 4 and memory | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/30 19:07 |